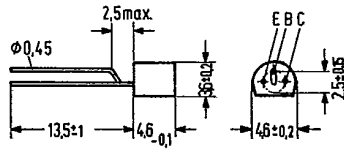


for large-signal VHF stages

BF 324 is an epitaxial PNP silicon planar transistor in TO 92 plastic package (10 A 3 DIN 41868). It is particularly outstanding for a low reverse transfer capacitance and is preferably used in common base configurations, e.g. in VHF tuner input stages.

Type	Ordering code
BF 324	Q62702-F311



Approx. weight 0.25 g Dimensions in mm

Maximum ratings

Collector-emitter voltage	$-V_{CEO}$	30	V
Collector-base voltage	$-V_{CBO}$	30	V
Emitter-base voltage	$-V_{EBO}$	4	V
Collector current	$-I_C$	25	mA
Base current	$-I_B$	5	mA
Junction temperature	T_J	150	°C
Storage temperature range	T_{stg}	-55 to +150	°C
Total power dissipation	P_{tot}	250	mW

Thermal resistance

Junction to ambient air	R_{thJA}	≤ 420	K/W
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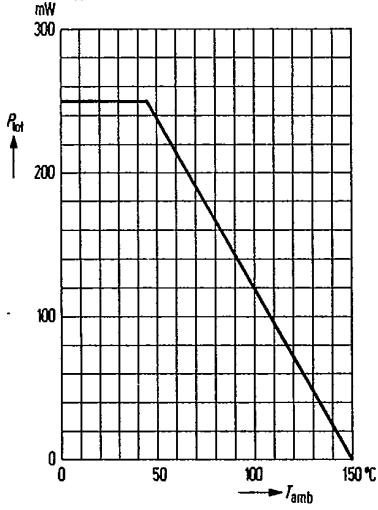
Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Collector cutoff current ($-V_{CB} = 30\text{ V}; I_E = 0$)	$-I_{CBO}$	<50	nA
Collector-emitter breakdown voltage ($-I_C = 10\text{ mA}; I_B = 0$)	$-V_{(BR)CEO}$	>30	V
Emitter-base breakdown voltage ($-I_E = 10\text{ }\mu\text{A}; I_C = 0$)	$-V_{(BR)EBO}$	>4	V
DC current gain ($-V_{CE} = 10\text{ V}; -I_C = 1\text{ mA}$)	h_{FE}	45	-
($-V_{CE} = 10\text{ V}; -I_C = 4\text{ mA}$)	h_{FE}	50 (25 to 160)	-
Base-emitter voltage ($-V_{CE} = 10\text{ V}; -I_C = 4\text{ mA}$)	$-V_{BE}$	0.76	V

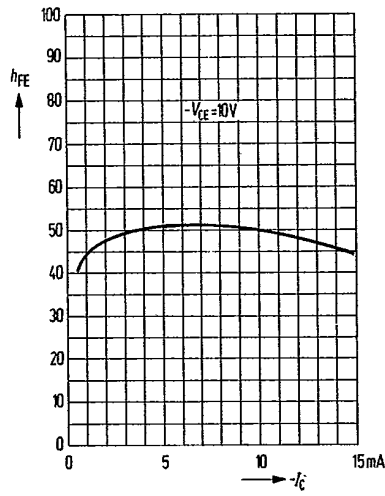
Dynamic characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Transition frequency ($f = 100\text{ MHz}$) ($-I_C = 1\text{ mA}; -V_{CE} = 10\text{ V}$)	f_T	350	MHz
($-I_C = 4\text{ mA}; -V_{CE} = 10\text{ V}$)	f_T	450	MHz
($-I_C = 8\text{ mA}; -V_{CE} = 10\text{ V}$)	f_T	440	MHz
Reverse transfer capacitance ($-V_{CB} = 10\text{ V}; -V_{BE} = 0; f = 1\text{ MHz}$)	C_{12b}	0.1	pF
Noise figure ($-I_C = 2\text{ mA}; -V_{CE} = 10\text{ V};$ $f = 100\text{ MHz}; R_g = 60\text{ }\Omega$)	NF	3	dB

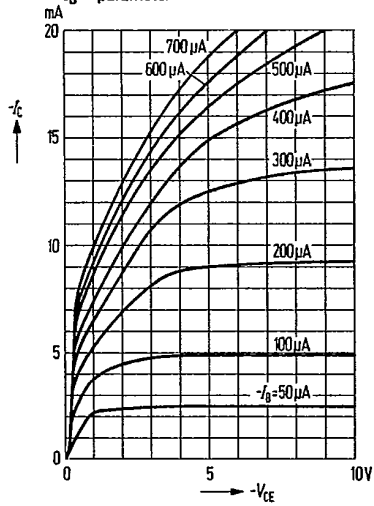
Total perm. power dissipation
 versus temperature
 $P_{tot} = f(T_{amb})$



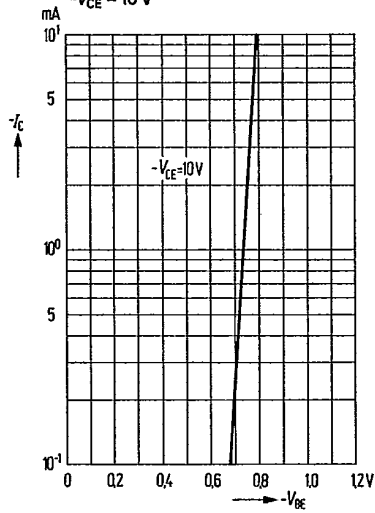
DC current gain $h_{FE} = f(I_C)$
 $-V_{CE} = 10V$



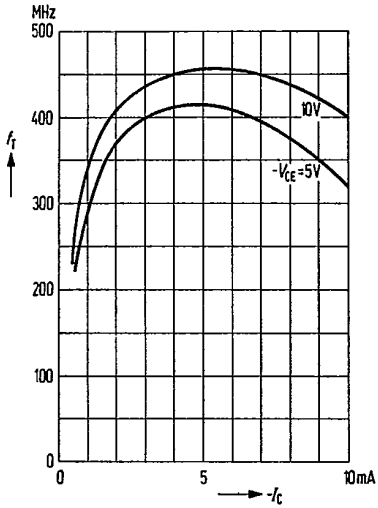
Output characteristics $I_C = f(V_{CE})$
 $I_B = \text{parameter}$



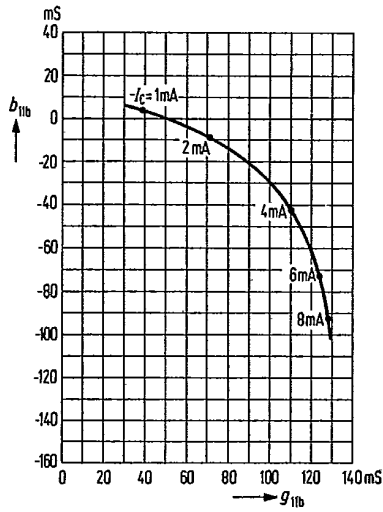
Input characteristic $I_C = f(V_{BE})$
 $-V_{CE} = 10V$



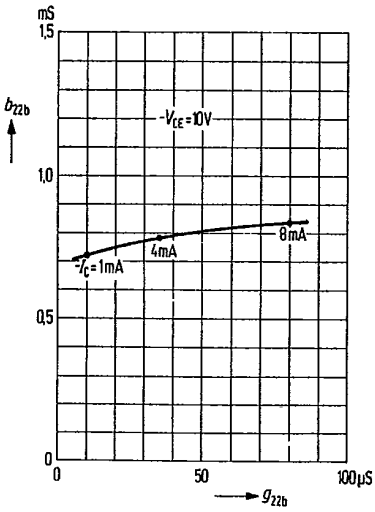
Transition frequency $f_T = f(f_C)$
 V_{CE} = parameter, $f = 100$ MHz



Input admittance Y_{11b}
(common base configuration)
 $f = 100$ MHz; $-V_{CE} = 10$ V



Output admittance Y_{22b}
(common base configuration)
 $f = 100$ MHz; $-V_{CE} = 10$ V



Short-circuit forward transfer admittance
 $Y_{21b} = f(f_C)$
(common base configuration)
 $-V_{CE} = 10$ V

